

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Patent Number:** 6,797,591

**Issued:** 09/28/2004

**Name of Patentee:** Gormley et al.

**Title of Invention:** METHOD FOR FORMING A SEMICONDUCTOR DEVICE AND A  
SEMICONDUCTOR DEVICE FORMED BY THE METHOD

**Attention Certificate of Corrections Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450**

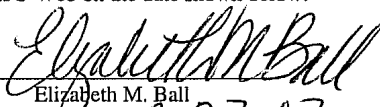
**SUPPLEMENTAL REQUEST FOR CERTIFICATE OF CORRECTION  
OF PATENT FOR PTO MISTAKE (37 CFR 1.322(a))**

1. Attached, in duplicate, is Form PTO-1050, with at least one copy being suitable for printing.
2. The exact page and line number where the errors are shown correctly in the application file are:

Page 18, line 18  
Page 19, line 9, 20  
Page 21, line 3  
Claim 38 as amended in an amendment mailed 1/24/03

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I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Patent and Trademark Office, via EFS-Web on the date shown below.

  
Elizabeth M. Ball  
Date: 2-27-07

3. Please send the Certificate to:

Name: Matthew E. Connors

Address: Gauthier & Connors, LLP

225 Franklin Street, Suite 2300

Boston, Massachusetts 02110

Reg. No.:33,298

SIGNATURE OF ATTORNEY

A handwritten signature in black ink, appearing to read "Matthew E. Connors", written over a horizontal line.

Matthew E. Connors  
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## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,797,591

DATED : 09/28/04

INVENTOR(S) : Gormley et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In Column 10, claim 10, line 64, delete "second stop layer being bonded to the one of the second and" and replace with " second etch stop layer being bonded to the one of the second and"

In Column 11, claim 17, line 18, delete "16" and replace with "15"

In Column 11, claim 20, line 30, delete " second and third layers and of semiconductor material." and replace with " second and third layers are of semiconductor material."

In Column 12, claim 31, line 23, delete the word "each" and insert the word "etch"


In Column 12, claim 38, line 48 , delete "first layer is at least half the area of the component in plan" and insert "first layer adjacent the component is at least half the area of the component in plan"

## MAILING ADDRESS OF SENDER:

Gauthier & Connors LLP  
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Boston, MA 02110

PATENT NO. 6,797,591

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